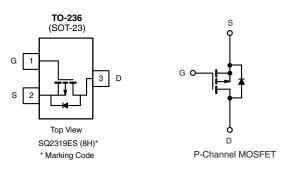
# **SQ2319ES**



**Vishay Siliconix** 

# Automotive P-Channel 40 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	- 40			
$R_{DS(on)} (\Omega)$ at $V_{GS} = -10 \text{ V}$	0.075			
$R_{DS(on)} (\Omega)$ at $V_{GS} = -4.5 V$	0.145			
I <sub>D</sub> (A)	- 4.6			
Configuration	Single			



### **FEATURES**

- Halogen-free According to IEC 61249-2-21
  Definition
- TrenchFET<sup>®</sup> Power MOSFET
- AEC-Q101 Qualified<sup>c</sup>
- 100 %  $R_{\rm q}$  and UIS Tested
- Compliant to RoHS Directive 2002/95/EC



KOHS COMPLIANT HALOGEN FREE

ORDERING INFORMATION	
Package	SOT-23
Lead (Pb)-free and Halogen-free	SQ2319ES-T1-GE3

<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>C</sub>	<sub>c</sub> = 25 °C, unles	s otherwise noted	)	
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V <sub>DS</sub>	- 40	v
Gate-Source Voltage		V <sub>GS</sub>	± 20	v
Continuous Drain Current	T <sub>C</sub> = 25 °C	- I <sub>D</sub>	- 4.6	
	T <sub>C</sub> = 125 °C		- 2.6	
Continuous Source Current (Diode Conduction)		I <sub>S</sub>	- 3.7	А
Pulsed Drain Current <sup>a</sup>		I <sub>DM</sub>	- 18	
Single Pulse Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	- 12	
Single Pulse Avalanche Energy		E <sub>AS</sub>	7.2	mJ
Maximum Power Dissipation <sup>a</sup>	T <sub>C</sub> = 25 °C	PD	3	W
	T <sub>C</sub> = 125 °C		1	VV V
Operating Junction and Storage Temperature Range	ge	T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 175	°C

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount <sup>b</sup>	R <sub>thJA</sub>	166	°C/W
nction-to-Foot (Drain)		R <sub>thJF</sub>	50	0/10

Notes

a. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%.$ 

b. When mounted on 1" square PCB (FR-4 material).

c. Parametric verification ongoing.

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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static	1					<b>I</b>	
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> :	V <sub>GS</sub> = 0, I <sub>D</sub> = - 250 μA		-	-	v
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	$V_{DS} = V_{GS}, I_D = -250 \ \mu A$		- 2.0	- 2.5	
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	$V_{DS} = 0 V, V_{GS} = \pm 20 V$		-	± 100	nA
Zero Gate Voltage Drain Current		$V_{GS} = 0 V$	V <sub>DS</sub> = - 40 V	-	-	- 1	
	I <sub>DSS</sub>	$V_{GS} = 0 V$	$V_{DS} = -40 \text{ V}, \text{ T}_{J} = 125 ^{\circ}\text{C}$	-	-	- 50	μA
		$V_{GS} = 0 V$	$V_{DS} = -40 \text{ V}, \text{ T}_{J} = 175 ^{\circ}\text{C}$	-	-	- 150	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = - 10 V	$V_{DS} \le$ - 5 V	- 10	-	-	Α
		V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 3 A	-	0.061	0.075	
Drain-Source On-State Resistance <sup>a</sup>		V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 3 A, T <sub>J</sub> = 125 °C	-	-	0.116	
	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 3 A, T <sub>J</sub> = 175 °C	-	-	0.139	Ω
		V <sub>GS</sub> = - 4.5 V	I <sub>D</sub> = - 2.4 A	-	0.120	0.145	
Forward Transconductanceb	9 <sub>fs</sub>	V <sub>DS</sub> :	= - 5 V, I <sub>D</sub> = - 3 A	-	8	-	S
Dynamic <sup>b</sup>		-			-		
Input Capacitance	C <sub>iss</sub>		V <sub>GS</sub> = 0 V V <sub>DS</sub> = - 25 V, f = 1 MHz	-	493	620	pF
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$		-	76	95	
Reverse Transfer Capacitance	C <sub>rss</sub>			-	51	65	
Total Gate Charge <sup>c</sup>	Qg		$V = V_{DS} = -20 V, I_{D} = -3 A$	-	10.5	16	nC
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = - 10 V		-	1.8	-	
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			-	2.6	-	
Gate Resistance	Rg	f = 1 MHz		5	10	15	Ω
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			-	5	8	
Rise Time <sup>c</sup>	t <sub>r</sub>	= חח	$V_{DD} = -20 \text{ V}, \text{ R}_{\text{I}} = 6.7 \Omega$		11	17	- ns
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong -3$ A, $V_{GEN} = -10$ V, $R_g = 1 \Omega$		-	19	29	
Fall Time <sup>c</sup>	t <sub>f</sub>			-	8	12	
Source-Drain Diode Ratings and Chara	acteristics <sup>b</sup>	•			•		
					-	10	^
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	- 18	A

Notes

a. Pulse test; pulse width  $\leq$  300  $\mu s,$  duty cycle  $\leq$  2 %.

b. Guaranteed by design, not subject to production testing.

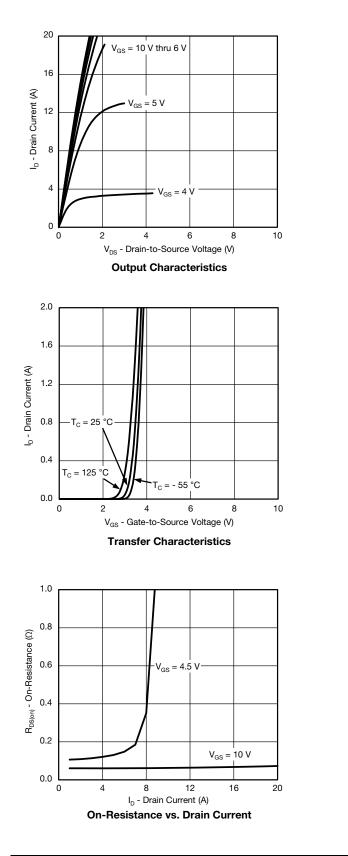
c. Independent of operating temperature.

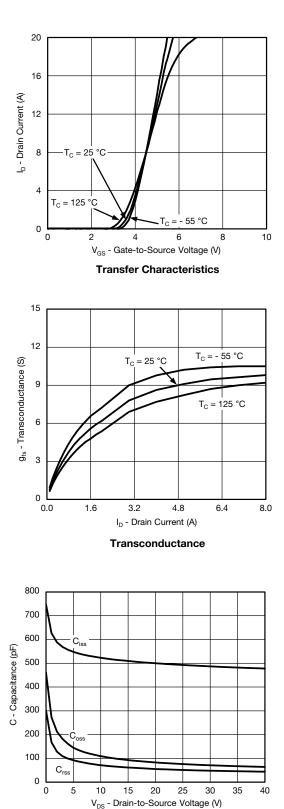
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



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## **TYPICAL CHARACTERISTICS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)





Capacitance

S11-2111-Rev. C, 07-Nov-11

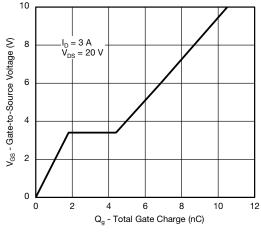
Document Number: 65735



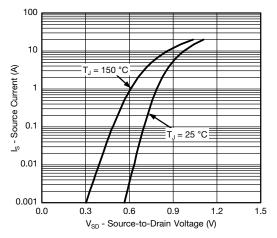
**SQ2319ES** 

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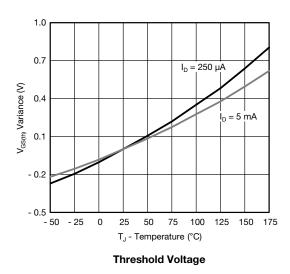
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)

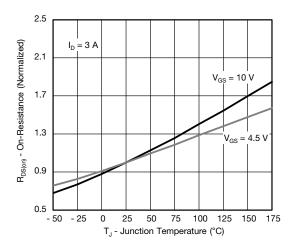


Gate Charge

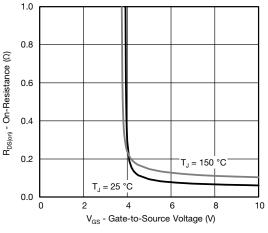


Source Drain Diode Forward Voltage

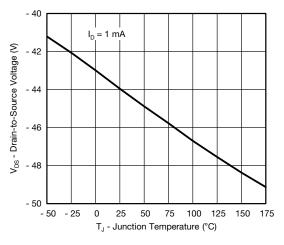




**On-Resistance vs. Junction Temperature** 



On-Resistance vs. Gate-to-Source Voltage



Drain Source Breakdown vs. Junction Temperature

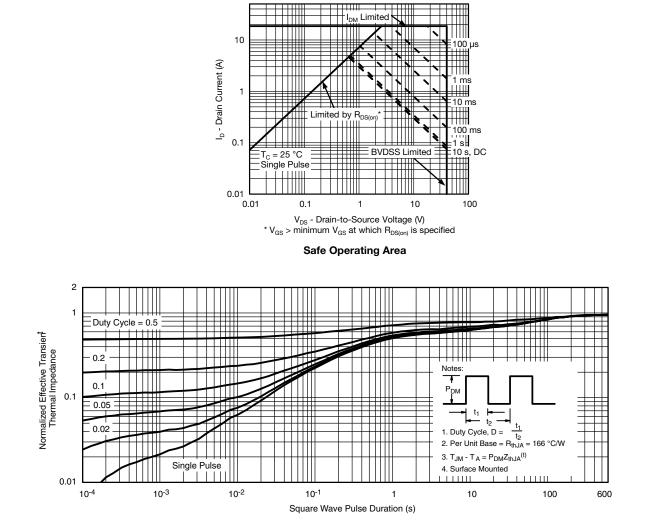
S11-2111-Rev. C, 07-Nov-11

Document Number: 65735



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## **THERMAL RATINGS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)

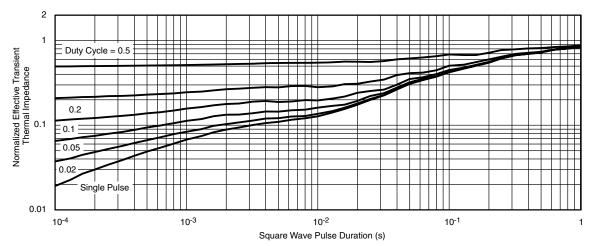


Normalized Thermal Transient Impedance, Junction-to-Ambient



# Vishay Siliconix

## **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Foot

#### Note

• The characteristics shown in the two graphs

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Foot (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="http://www.vishay.com/ppg?65735">www.vishay.com/ppg?65735</a>.



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